

## NCE N-Channel Enhancement Mode Power MOSFET

## **Description**

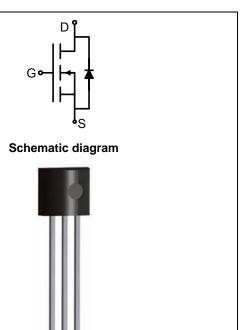
The NCE0202ZA uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

#### **General Features**

- $V_{DS}$  = 200V, $I_D$  =2A  $R_{DS(ON)}$  < 580mΩ @  $V_{GS}$ =10V (Typ:520mΩ)
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

# **Application**

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



TO-92 view

## **Package Marking and Ordering Information**

| Device Marking | Device    | Device Package | Reel Size | Tape width | Quantity |
|----------------|-----------|----------------|-----------|------------|----------|
| N0202          | NCE0202ZA | TO-92          | -         | -          | -        |

Absolute Maximum Ratings (T<sub>A</sub>=25 ℃unless otherwise noted)

| Parameter  | Symbol              | Limit      | Unit   |
|--|---------------------|------------|--|
| Drain-Source Voltage                             | V <sub>DS</sub>     | 200        | V  |
| Gate-Source Voltage                              | V <sub>GS</sub>     | ±20        | V  |
| Drain Current-Continuous                         | I <sub>D</sub>      | 2          | Α  |
| Drain Current-Pulsed (Note 1)                    | I <sub>DM</sub>     | 8          | Α  |
| Maximum Power Dissipation                        | P <sub>D</sub>      | 3          | W  |
| Operating Junction and Storage Temperature Range | $T_{J}$ , $T_{STG}$ | -55 To 150 | $^{\circ}\!$ |

#### **Thermal Characteristic**

| Thermal Resistance, Junction-to-Ambient (Note 2) | $R_{	heta JA}$ | 41.7 | °C/W |
|--|----------------|------|------|
|  | 00/1           |      | i e  |

# **Electrical Characteristics (T<sub>A</sub>=25**°C unless otherwise noted)

| Parameter                       | Symbol            | Condition                                 | Min | Тур | Max | Unit |
|---------------------------------|-------------------|---|-----|-----|-----|------|
| Off Characteristics             |                   |   |     |     |     |      |
| Drain-Source Breakdown Voltage  | BV <sub>DSS</sub> | V <sub>GS</sub> =0V I <sub>D</sub> =250μA | 200 | -   | -   | V    |
| Zero Gate Voltage Drain Current | I <sub>DSS</sub>  | V <sub>DS</sub> =200V,V <sub>GS</sub> =0V | -   | -   | 1   | μA   |



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# NCE0202ZA

| Gate-Body Leakage Current          | I <sub>GSS</sub>    | I <sub>GSS</sub> V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V |     | -   | ±100 | nA |  |
|------------------------------------|---------------------|--|-----|-----|------|----|--|
| On Characteristics (Note 3)        |                     |  |     |     |      |    |  |
| Gate Threshold Voltage             | V <sub>GS(th)</sub> | V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250μA    | 1.2 | 1.8 | 2.5  | V  |  |
| Drain-Source On-State Resistance   | R <sub>DS(ON)</sub> | V <sub>GS</sub> =10V, I <sub>D</sub> =2A                   | -   | 520 | 580  | mΩ |  |
| Forward Transconductance           | <b>g</b> FS         | V <sub>DS</sub> =15V,I <sub>D</sub> =2A                    | -   | 8   | -    | S  |  |
| Dynamic Characteristics (Note4)    |                     |  |     |     |      |    |  |
| Input Capacitance                  | C <sub>lss</sub>    | V <sub>DS</sub> =25V,V <sub>GS</sub> =0V,                  | -   | 580 | -    | PF |  |
| Output Capacitance                 | C <sub>oss</sub>    | V <sub>DS</sub> -23V,V <sub>GS</sub> -0V,<br>F=1.0MHz      | -   | 90  | -    | PF |  |
| Reverse Transfer Capacitance       | C <sub>rss</sub>    | F=1.0WHZ   | -   | 3   | -    | PF |  |
| Switching Characteristics (Note 4) |                     |  |     |     |      |    |  |
| Turn-on Delay Time                 | t <sub>d(on)</sub>  |  | -   | 10  | -    | nS |  |
| Turn-on Rise Time                  | t <sub>r</sub>      | $V_{DD}$ =100V, $R_L$ =15 $\Omega$                         | -   | 12  | -    | nS |  |
| Turn-Off Delay Time                | $t_{d(off)}$        | $V_{GS}$ =10 $V$ , $R_{G}$ =2.5 $\Omega$                   | -   | 15  | -    | nS |  |
| Turn-Off Fall Time                 | t <sub>f</sub>      |  | -   | 15  | -    | nS |  |
| Total Gate Charge                  | $Q_g$               | \/ -100\/   -24  | -   | 12  |      | nC |  |
| Gate-Source Charge                 | $Q_{gs}$            | $V_{DS}$ =100V, $I_{D}$ =2A,<br>$V_{GS}$ =10V              | -   | 2.5 | -    | nC |  |
| Gate-Drain Charge                  | Q <sub>gd</sub>     | VGS-10V  | -   | 3.8 | -    | nC |  |
| Drain-Source Diode Characteristics | ·                   |  |     |     |      |    |  |
| Diode Forward Voltage (Note 3)     | V <sub>SD</sub>     | V <sub>GS</sub> =0V,I <sub>S</sub> =2A                     | -   | -   | 1.2  | V  |  |
| Diode Forward Current (Note 2)     | Is                  |  |     | -   | 2    | Α  |  |

### Notes:

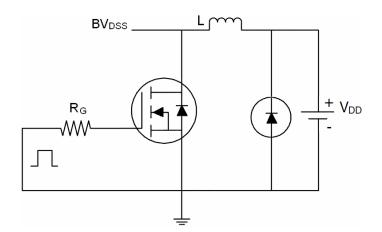
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production

**Pb Free Product** 

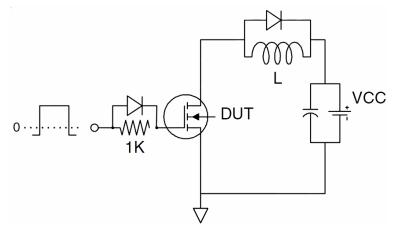


# **Test Circuit**

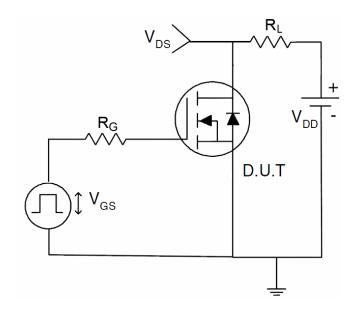
# 1) E<sub>AS</sub> test circuit



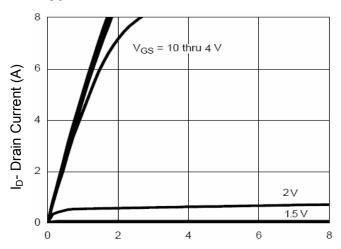
# 2) Gate charge test circuit



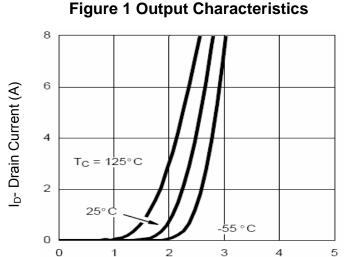
### 3) Switch Time Test Circuit



# **Typical Electrical and Thermal Characteristics (Curves)**



Vds Drain-Source Voltage (V)



Vgs Gate-Source Voltage (V)
Figure 2 Transfer Characteristics

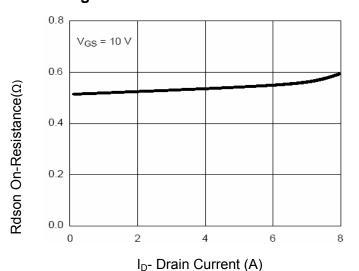
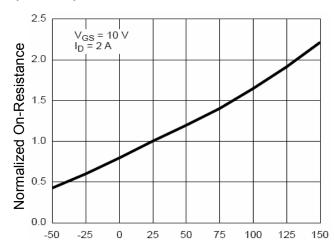


Figure 3 Rdson- Drain Current



 $T_J$ -Junction Temperature (°C) **Figure 4 Rdson-JunctionTemperature** 

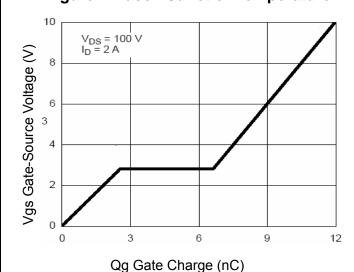


Figure 5 Gate Charge

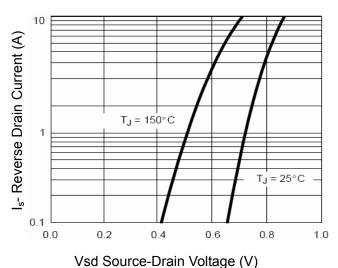
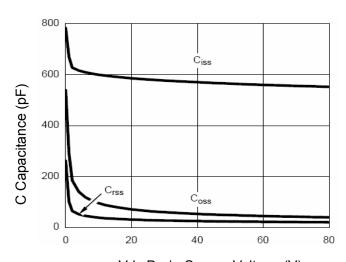
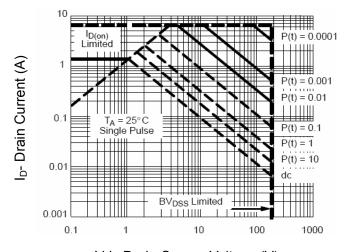


Figure 6 Source- Drain Diode Forward



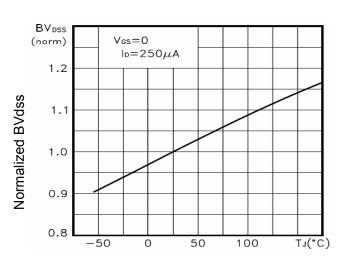
Vds Drain-Source Voltage (V)

Figure 7 Capacitance vs Vds



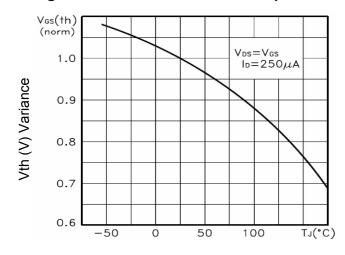
Vds Drain-Source Voltage (V)

**Figure 8 Safe Operation Area** 



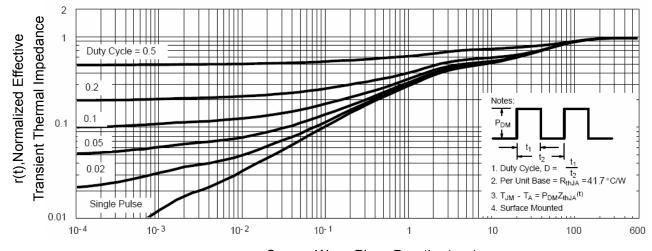
T<sub>J</sub>-Junction Temperature(°C)

Figure 9 BV<sub>DSS</sub> vs Junction Temperature



T<sub>J</sub>-Junction Temperature(°C)

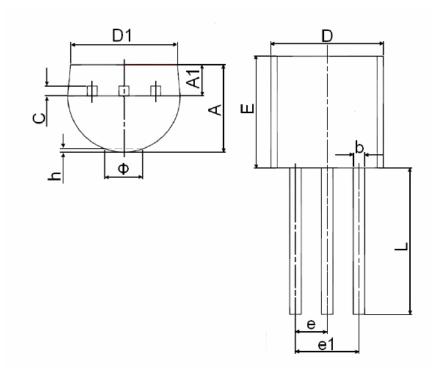
Figure 10 V<sub>GS(th)</sub> vs Junction Temperature



Square Wave Pluse Duration(sec)

**Figure 11 Normalized Maximum Transient Thermal Impedance** 

# **TO-92 Package Information**



| Symbol | Dimensions | In Millimeters | Dimensions In Inches |       |  |  |
|--------|------------|----------------|----------------------|-------|--|--|
| Symbol | Min        | Max            | Min                  | Max   |  |  |
| Α      | 3.300      | 3.700          | 0.130                | 0.146 |  |  |
| A1     | 1.100      | 1.400          | 0.043                | 0.055 |  |  |
| b      | 0.380      | 0.550          | 0.015                | 0.022 |  |  |
| С      | 0.360      | 0.510          | 0.014                | 0.020 |  |  |
| D      | 4.400      | 4.700          | 0.173                | 0.185 |  |  |
| D1     | 3.430      |                | 0.135                |       |  |  |
| Е      | 4.300      | 4.700          | 0.169                | 0.185 |  |  |
| е      | 1.270      | TYP            | 0.050 TYP            |       |  |  |
| e1     | 2.440      | 2.640          | 0.096                | 0.104 |  |  |
| L      | 14.100     | 14.500         | 0.555                | 0.571 |  |  |
| Ф      |            | 1.600          |                      | 0.063 |  |  |
| h      | 0.000      | 0.380          | 0.000                | 0.015 |  |  |

#### **Notes**

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- $5. \ Controlling \ dimension \ is \ millimeter, \ converted \ inch \ dimensions \ are \ not \ necessarily \ exact.$

**Pb-Free Product** 

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